

# 2SD1010

## Silicon NPN epitaxial planer type

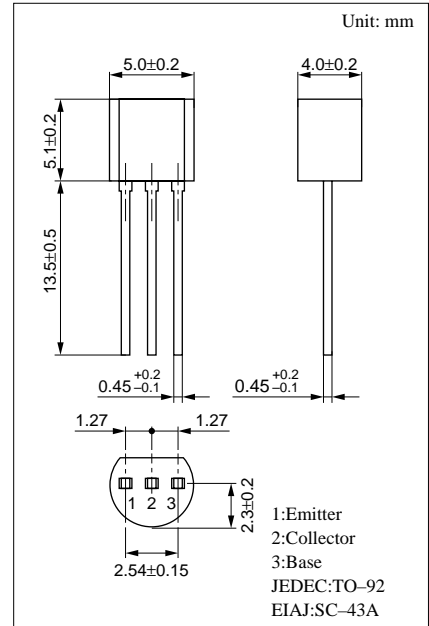
For low-frequency amplification

### Features

- High forward current transfer ratio  $h_{FE}$ .
- Low collector to emitter saturation voltage  $V_{CE(sat)}$ .
- High emitter to base voltage  $V_{EBO}$ .
- Low noise voltage NV.

### Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	50	V
Collector to emitter voltage	$V_{CEO}$	40	V
Emitter to base voltage	$V_{EBO}$	15	V
Peak collector current	$I_{CP}$	100	mA
Collector current	$I_C$	50	mA
Collector power dissipation	$P_C$	300	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 ~ +150	°C



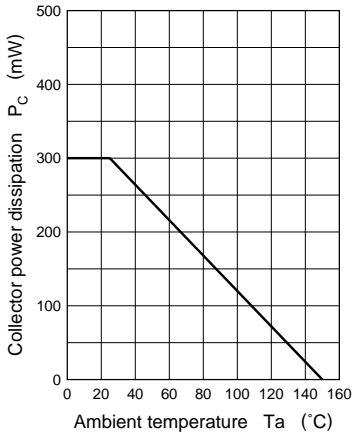
### Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = 20V, I_E = 0$			100	nA
	$I_{CEO}$	$V_{CE} = 20V, I_B = 0$			1	μA
Collector to base voltage	$V_{CBO}$	$I_C = 10\mu A, I_E = 0$	50			V
Collector to emitter voltage	$V_{CEO}$	$I_C = 1mA, I_B = 0$	40			V
Emitter to base voltage	$V_{EBO}$	$I_E = 10\mu A, I_C = 0$	15			V
Forward current transfer ratio	$h_{FE}^*$	$V_{CE} = 10V, I_C = 2mA$	400	1000	2000	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10mA, I_B = 1mA$		0.05	0.2	V
Transition frequency	$f_T$	$V_{CB} = 10V, I_E = -2mA, f = 200MHz$		200		MHz
Noise voltage	NV	$V_{CE} = 10V, I_C = 1mA, G_V = 80dB$ $R_g = 100k\Omega, \text{Function} = \text{FLAT}$		80		mV

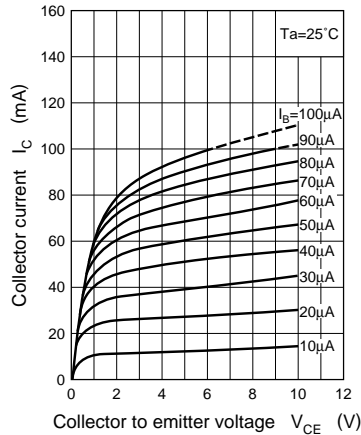
\* $h_{FE}$  Rank classification

Rank	R	S	T
$h_{FE}$	400 ~ 800	600 ~ 1200	1000 ~ 2000

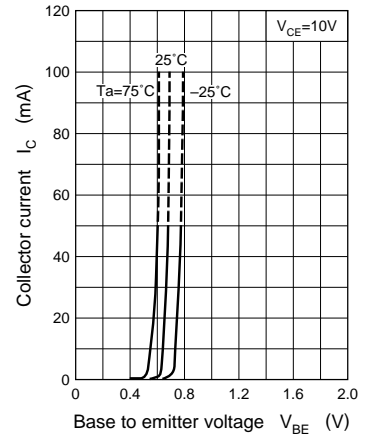
$P_C - T_a$



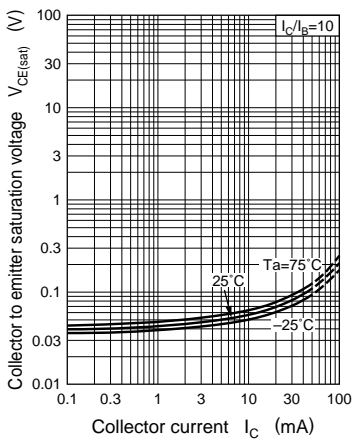
$I_C - V_{CE}$



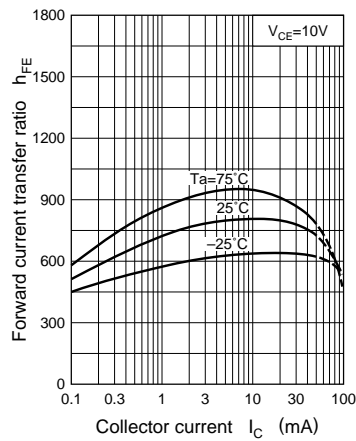
$I_C - V_{BE}$



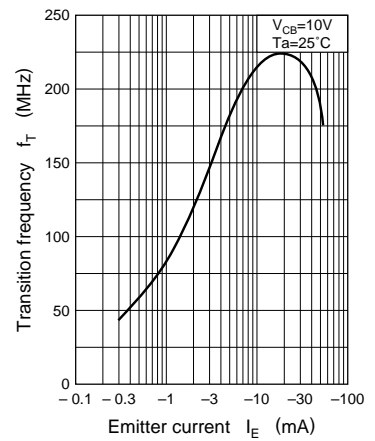
$V_{CE(sat)} - I_C$



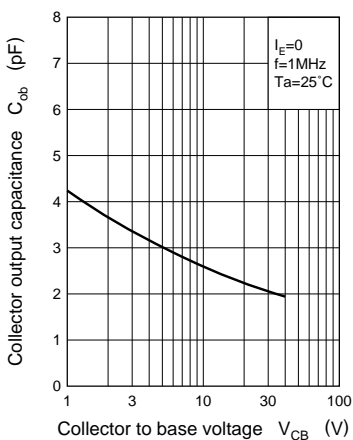
$h_{FE} - I_C$



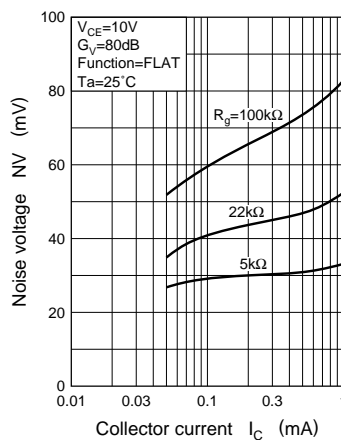
$f_T - I_E$



$C_{ob} - V_{CB}$



$NV - I_C$



$NV - V_{CE}$

